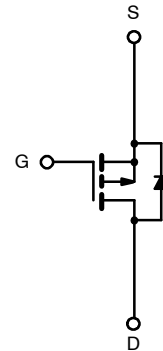
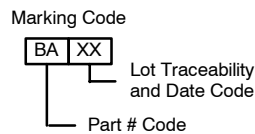
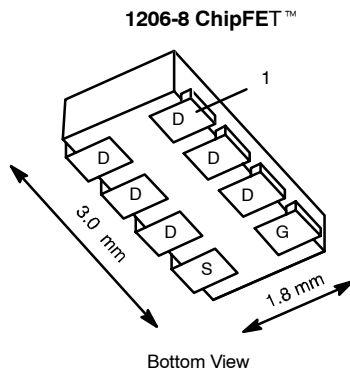




P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.055 @ $V_{GS} = -4.5$ V	± 5.3
	0.06 @ $V_{GS} = -3.6$ V	± 5.1
	0.083 @ $V_{GS} = -2.5$ V	± 4.3

TrenchFET®
Power MOSFETs
2.5-V Rated



P-Channel MOSFET

Ordering Information: Si5441DC-T1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	5 secs	Steady State
Drain-Source Voltage		V_{DS}	-20	
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	± 5.3	± 3.9
	$T_A = 85^\circ\text{C}$		± 3.8	± 2.8
Pulsed Drain Current		I_{DM}	± 20	
Continuous Source Current ^a		I_S	-2.1	-1.1
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	2.5	1.3
	$T_A = 85^\circ\text{C}$		1.3	0.7
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	
Soldering Recommendations (Peak Temperature) ^{b, c}			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	40	50	$^\circ\text{C/W}$
	Steady State		80	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	15	20	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

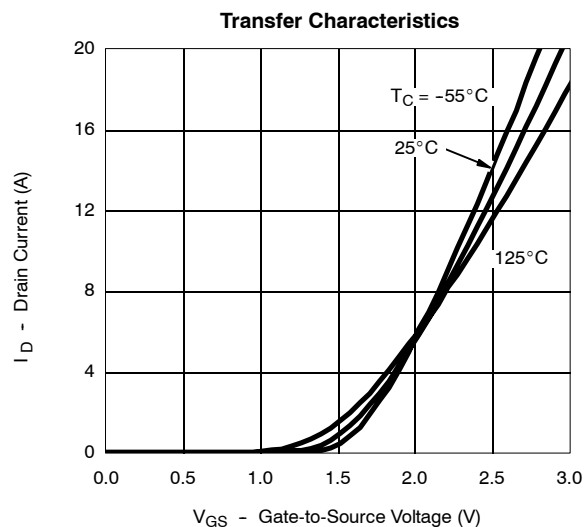
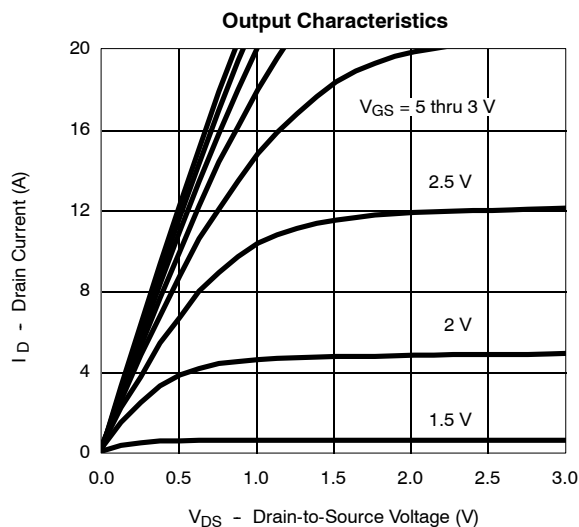
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16\ \text{V}, V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -16\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	-20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -3.9\ \text{A}$		0.046	0.055	Ω
		$V_{GS} = -3.6\ \text{V}, I_D = -3.7\ \text{A}$		0.050	0.06	
		$V_{GS} = -2.5\ \text{V}, I_D = -3.1\ \text{A}$		0.070	0.083	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}, I_D = -3.9\ \text{A}$		12		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.1\ \text{A}, V_{GS} = 0\ \text{V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -3.9\ \text{A}$		11	22	nC
Gate-Source Charge	Q_{gs}			3.0		
Gate-Drain Charge	Q_{gd}			2.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\ \text{V}, R_L = 10\ \Omega$ $I_D \cong -1\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_G = 6\ \Omega$		20	30	ns
Rise Time	t_r			35	55	
Turn-Off Delay Time	$t_{d(off)}$			65	100	
Fall Time	t_f			45	70	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.1\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		30	60	

Notes

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

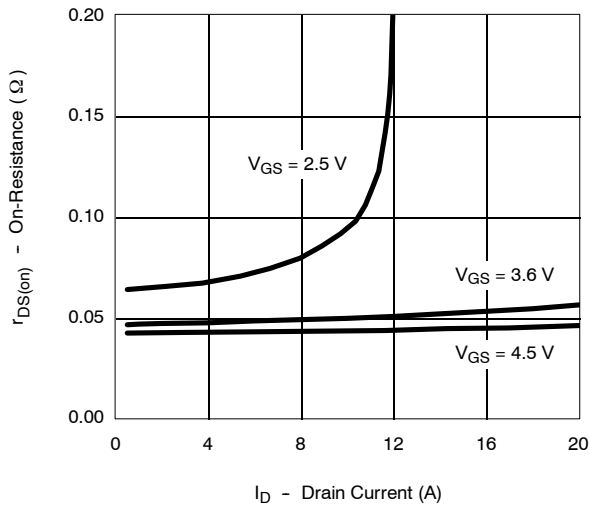
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

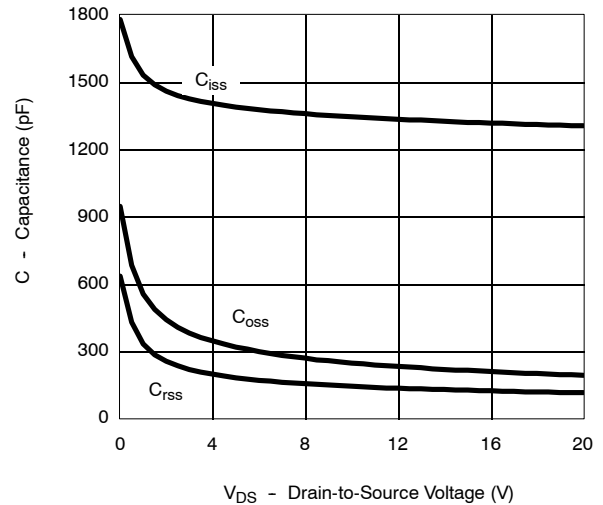


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

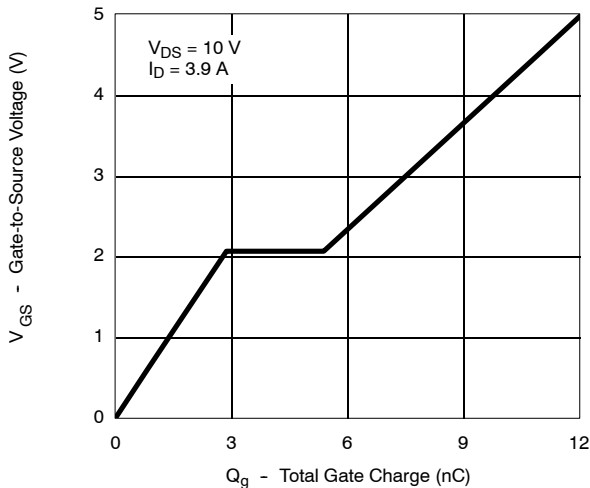
On-Resistance vs. Drain Current



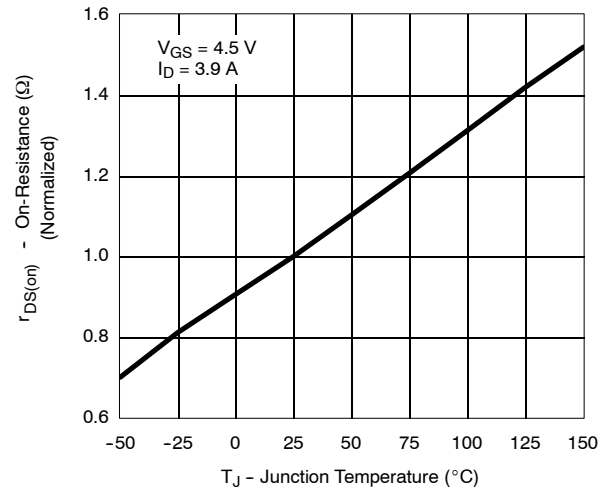
Capacitance



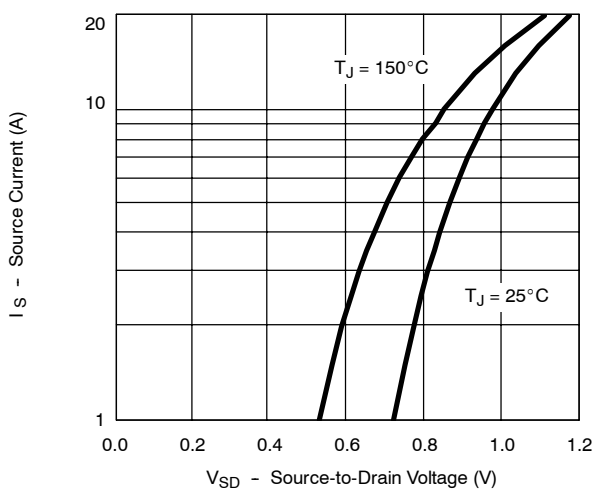
Gate Charge



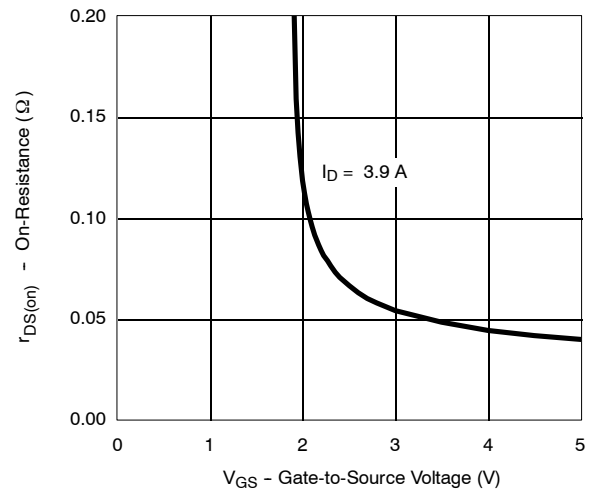
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

